2-Input AND Gate with Open Drain Output

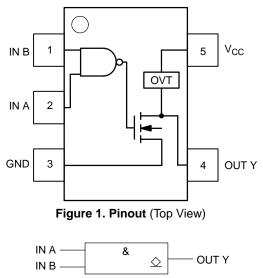
The MC74VHC1G09E is an advanced high speed CMOS 2–input AND gate with open drain output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including an open drain output which provides the capability to set output switching level. This allows the MC74VHC1G09E to be used to interface 5 V circuits to circuits of any voltage between V_{CC} and 5.5 V using an external resistor and power supply.

The MC74VHC1G09E input structure provides protection when voltages up to 5.5 V are applied, regardless of the supply voltage.

Features

- High Speed: $t_{PD} = 4.3$ ns (Typ) at $V_{CC} = 5$ V
- Low Internal Power Dissipation: $I_{CC} = 1 \ \mu A$ (Max) at $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 62; Equivalent Gates = 16
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant







ON Semiconductor®

www.onsemi.com

MARKING DIAGRAMS





SC-88A / SOT-353 / SC-70 DF SUFFIX CASE 419A

> VX = Device Code M = Date Code*

= Pb–Free Package

(Note: Microdot may be in either location) *Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT				
1	IN B			
2	IN A			
3	GND			
4	OUT Y			
5	V _{CC}			

FUNCTION TABLE

Inp	uts	Output
Α	в	Y
L	L	L
L	н	L
н	L	L
Н	Н	Z

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Characteristics	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +6.5	V
V _{IN}	DC Input Voltage	-0.5 to +6.5	V
V _{OUT}	DC Output Voltage	-0.5 to +6.5	V
I _{IK}	Input Diode Current	-20	mA
I _{OK}	Output Diode Current	+20	mA
I _{OUT}	DC Output Current, per Pin	+25	mA
Icc	DC Supply Current, V _{CC} and GND	+50	mA
PD	Power dissipation in still air	200	mW
θ_{JA}	Thermal resistance	333	°C/W
ΤL	Lead temperature, 1 mm from case for 10 s	260	°C
TJ	Junction temperature under bias	+150	°C
T _{stg}	Storage temperature	-65 to +150	°C
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 28 to 34	UL 94 V–0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage Human Body Model (Note 1) Charged Device Model (Note 2)	4000 1000	V
I _{Latchup}	Latchup Performance Above V _{CC} and Below GND at 125°C (Note 3)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Tested to EIA/JESD22-A114-A

2. Tested to JESD22-C101-A

3. Tested to EIA/JESD78

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{IN}	DC Input Voltage	0.0	5.5	V
V _{OUT}	DC Output Voltage	0.0	7.0	V
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Rise and Fall Time $\begin{array}{ll} V_{CC}=3.3~V\pm0.3~V\\ V_{CC}=5.0~V\pm0.5~V \end{array}$	0 0	10 5	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			v _{cc}	٦	T _A = 25°C		$T_{A} = 25^{\circ}C \qquad \qquad T_{A} \le 85^{\circ}C$		85°C	$-55 \leq T_A \leq 125^\circ C$		
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit	
VIH	Minimum High–Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V	
V _{IL}	Maximum Low–Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V	
V _{OL}	$\begin{array}{l} \mbox{Maximum Low-Level} \\ \mbox{Output Voltage} \\ \mbox{V}_{\rm IN} = \mbox{V}_{\rm IH} \mbox{ or } \mbox{V}_{\rm IL} \end{array}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V	
I _{IN}	Maximum Input Leakage Current	V_{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA	
I _{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		20		40	μΑ	
I _{OFF}	Power Off–Output Leakage Current	V _{OUT} = 5.5 V V _{IN} = 5.5 V	0			0.25		2.5		5	μΑ	

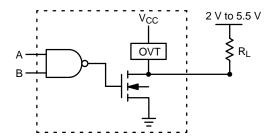
AC ELECTRICAL CHARACTERISTICS Input $t_{\text{f}} = t_{\text{f}} = 3.0 \text{ ns}$

			٦	T _A = 25°C		T _A ≤	85°C	–55 ≤ T _A	≤ 125°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PZL}	Maximum Output Enable Time, Input A or B to Y	$ \begin{array}{l} {\sf V}_{CC} = 3.3 \pm 0.3 \; {\sf V} \; {\sf C}_L = 15 \; {\sf pF} \\ {\sf R}_L = 1000 \; \Omega \qquad {\sf C}_L = 50 \; {\sf pF} \end{array} $		6.2 8.7	8.8 12.3		10.5 14.0		12.5 16.5	ns
		$ \begin{array}{c} V_{CC} = 5.0 \pm 0.5 \ V \ C_L = 15 \ pF \\ R_L = 1000 \ \Omega \qquad C_L = 50 \ pF \end{array} $		4.3 5.8	5.9 7.9		7.0 9.0		9.0 11.0	
t _{PLZ}	Maximum Output Disable Time			8.7	12.3		14.0		16.5	ns
				5.8	7.9		9.0		11.0	
C _{IN}	Maximum Input Ca- pacitance			6.0	10		10		10	pF
					·	Турі	cal @ 2	5°C, V _{CC} =	5.0 V	

 CPD
 Power Dissipation Capacitance (Note 4)
 18
 pF

 4. CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

4. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



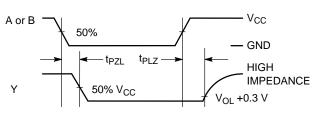
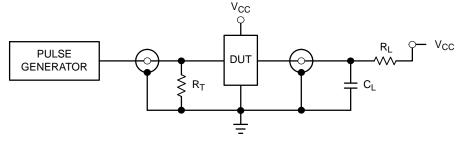


Figure 3. Output Voltage Mismatch Application



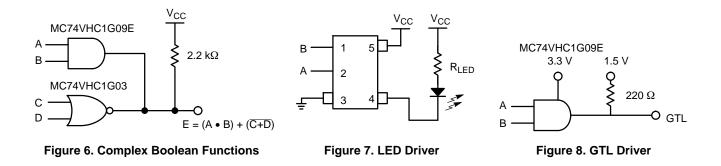


 C_L = 50 pF equivalent (Includes jig and probe capacitance)

 $R_L = 1000 \Omega$ or equivalent

 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 5. Test Circuit

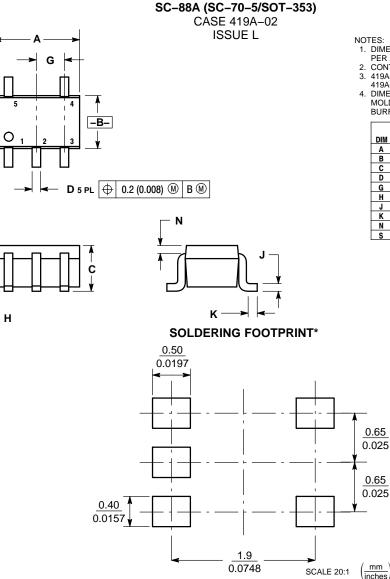


ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHC1G09EDFT2G	SC70–5 / SC–88A / SOT–353 (Pb–Free)	3000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor dates sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights or the rights of others. ON Semiconductor and in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or deat

Phone: 421 33 790 2910

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

S

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

ON Semiconductor Website: www.onsemi.com

NOTES: 1. DIMENSIONING AND TOLERANCING DEP ANSI X14 5M 1982

PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

 419A–01 OBSOLETE. NEW STANDARD 419A–02.

419A-02. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INC	HES	MILLIN	ETERS	
DIM	MIN	MIN MAX		MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026	BSC	0.65	BSC	
Η		0.004		0.10	
L	0.004	0.010	0.10	0.25	
Κ	0.004	0.012	0.10	0.30	
Ν	0.008 REF		0.20	REF	
s	0.079	0.087	.087 2.00		